

L Number	Hits	Search Text	DB	Time stamp
1	7303	(nonvolatile non adj volatile) with (trench hole recess via groove opening)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 07:36
2	868	((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:00
3	743	(((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:00
4	433	(((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:01
5	364	((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:02
6	320	((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:03
7	317	(((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:03
8	314	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:19
9	262	((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and silicon adj (nitride oxide)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:06
12	13	(((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and sacrificial with (silicon adj (nitride oxide))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:07
11	32	(((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and sacrificial	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:08
13	183	(((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and (expos\$4 near4 substrate)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:34
14	56	((((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and (expos\$4 near4 substrate)) and plug	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:20

10	12	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and sacrificial with (trench hole via recess opening)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:27
15	206	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and (expos\$4 near4 (conduct\$4 substrate))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:34
16	179	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and silicon adj (nitride oxide)) and (expos\$4 near4 (conduct\$4 substrate))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:34
17	52	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and silicon adj (nitride oxide)) and (expos\$4 near4 (conduct\$4 substrate))) and plug	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:34
18	12	(nonvolatile non adj volatile) with (source near4 plug)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 07:20
19	277	(memory) with (source near4 plug)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 07:30
20	13	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and (source near4 plug)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 07:33
21	2039	split adj gate	USPAT; US-PGPUB; EPO; JPO	2004/10/20 07:33
22	2	(split adj gate) with source near plug	USPAT; US-PGPUB; EPO; JPO	2004/10/20 07:34
23	161	((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and split adj gate	USPAT; US-PGPUB; EPO; JPO	2004/10/20 08:00
24	5	"6271088"	USPAT; US-PGPUB; EPO; JPO	2004/10/20 08:02
25	19	"6204126"	USPAT; US-PGPUB; EPO; JPO	2004/10/20 08:21
26	8	"6143606"	USPAT; US-PGPUB; EPO; JPO	2004/10/20 08:21
27	1		USPAT	2004/10/20 08:22
28	1		USPAT	2004/10/20 08:22
29	0		USPAT	2004/10/20 08:26
30	1		USPAT	2004/10/20 08:26
31	1		USPAT	2004/10/20 08:26
32	1		USPAT	2004/10/20 08:26
33	1		USPAT	2004/10/20 08:30
34	1		USPAT	2004/10/20 08:30
35	1		USPAT	2004/10/20 08:30
36	1		USPAT	2004/10/20 08:30

L Number	Hits	Search Text	DB	Time stamp
1	7303	(nonvolatile non adj volatile) with (trench hole recess via groove opening)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 05:59
2	868	((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:00
3	743	((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3)))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:00
4	433	(((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening)))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:01
5	364	((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:02
6	320	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:03
7	317	(((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:03
8	314	((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate) and (dielectric insulat\$5)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:19
9	262	((((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and silicon adj (nitride oxide)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:06
12	13	(((((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and sacrificial with (silicon adj (nitride oxide)))	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:07
11	32	(((((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and sacrificial	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:08
13	183	(((((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and (expos\$4 near4 substrate)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:20
14	56	((((((((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control)))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and (expos\$4 near4 substrate)) and plug	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:20

10	12	((((((((nonvolatile non adj volatile) with (trench hole recess via groove opening)) and (etch\$3 with (trench hole recess via groove opening))) and (etch\$3 with (photoresist resist mask\$3))) and ((spacer sidewall side adj wall) with (trench hole recess via groove opening))) and (gate near3 (floating control))) and conduct\$4) and substrate) and (dielectric insulat\$5)) and sacrificial with (trench hole via recess opening)	USPAT; US-PGPUB; EPO; JPO	2004/10/20 06:27
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